

Acceleration

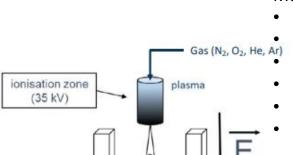
zone (35 kV)

Implantation zone (35 kV)

Ion Implantation for Innovative Interface modifications in BAttery and Graphene-enabled Systems

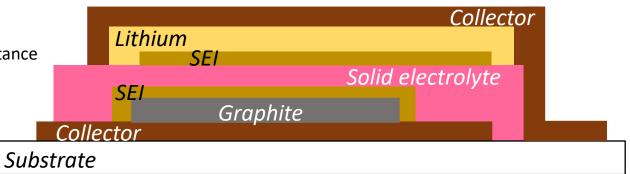
Low Energy Ion Implantation

Reference device structure



Monitoring material properties

- Surface hardening
- Improved corrosion and HT oxidation resistance
 - Wettability modification
- Adhesion improvement at interfaces
- Enhancing barrier properties (polymers)
 - Doping and allowing (oxides, nitride...)



Graphite electrode (cathode):

TRL 2-4

- Non-reactive implantation: Ne, Ar for monitoring vacancies in graphite
- Reactive implantation: N for doping

Solid state electrolytes:

Materials and fabrication methods: Li-PEO (Wet X) and LIPON (PVD) Non-reactive ion implantation for monitoring ionic transport: Species: Ar, N, He, Ne Electrical characterization with impedance spectroscopy (Biologic, Modulab)

Implanted species: all kind of gaseous compound Operating environment: high vacuum (~10-5 Torr)

Energy range: 10 keV to 40 keV

Dose (fluence): 10¹⁴ cm⁻² to 10¹⁸ cm⁻²

Near surface implantation: up to 500 nm

Li electrode (anode):

Deposition of Li layer (μ m) and additional interfacial thin film (LiF, MoS₂) lon implantation for monitoring stability upon cycling Non-reactive implantation vs. Reactive implantation (H₂S, CF₄)

Characterization of lavers in half cells: electrical properties, capacity & energy, (de)charging time, stability in cycling









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